

**MMBF4860**

**CASE 318-02/03, STYLE 10  
SOT-23 (TO-236AA/AB)**

**FET  
SWITCHING TRANSISTOR**

**N-CHANNEL**

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V <sub>dc</sub>
Drain-Gate Voltage	V <sub>DG</sub>	30	V <sub>dc</sub>
Reverse Gate-Source Voltage	V <sub>GS(r)</sub>	30	V <sub>dc</sub>
Forward Gate Current	I <sub>G(f)</sub>	50	mAdc

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
*Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	350 2.8	mW mW/°C
Storage Temperature	T <sub>stg</sub>	150	°C
*Thermal Resistance Junction to Ambient	R <sub>θJA</sub>	357	°C/W

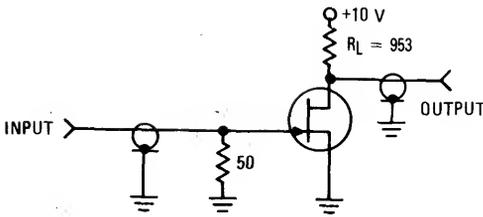
\*Package mounted on 99.5% alumina 10 x x 0.6 mm.

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)**

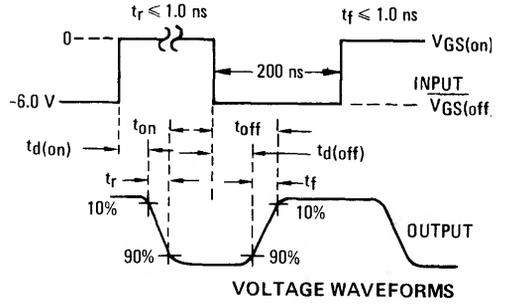
Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Gate-Source Breakdown Voltage (I <sub>G</sub> = 1.0 μAdc, V <sub>DS</sub> = 0)	V <sub>(BR)GSS</sub>	30	—	V <sub>dc</sub>
Gate Reverse Current (V <sub>GS</sub> = 15 V <sub>dc</sub> , V <sub>DS</sub> = 0) (V <sub>GS</sub> = 15 V <sub>dc</sub> , V <sub>DS</sub> = 0, T <sub>A</sub> = 150°C)	I <sub>GSS</sub>	—	0.5 2.0	nAdc μAdc
Gate Source Cutoff Voltage (V <sub>DS</sub> = 15 V <sub>dc</sub> , I <sub>D</sub> = 0.5 nAdc)	V <sub>GS(off)</sub>	2.0	6.0	V <sub>dc</sub>
<b>ON CHARACTERISTICS</b>				
Zero-Gate-Voltage Drain(1) (V <sub>DS</sub> = 15 V <sub>dc</sub> , V <sub>GS</sub> = 0)	I <sub>DSS</sub>	20	100	mAdc
Drain Cutoff Current (V <sub>DS</sub> = 15 V <sub>dc</sub> , V <sub>GS</sub> = 10 V <sub>dc</sub> ) (V <sub>DS</sub> = 15 V <sub>dc</sub> , V <sub>GS</sub> = 10 V <sub>dc</sub> , T <sub>A</sub> = 150°C)	I <sub>D(off)</sub>	—	0.25 0.5	nAdc μAdc
Drain-Source On-Voltage (I <sub>D</sub> = 10 mAdc, V <sub>GS</sub> = 0)	V <sub>DS(on)</sub>	—	0.5	V <sub>dc</sub>
Static Drain-Source On Resistance (V <sub>GS</sub> = 0, I <sub>D</sub> = 0, f = 1.0 kHz)	r <sub>DS(on)</sub>	—	40	Ohms
Input Capacitance (V <sub>DS</sub> = 0, V <sub>GS</sub> = 10 V <sub>dc</sub> , f = 1.0 MHz)	C <sub>iss</sub>	—	18	pF
Reverse Transfer Capacitance (V <sub>DS</sub> = 0, V <sub>GS</sub> = 10 V <sub>dc</sub> , f = 1.0 MHz)	C <sub>rss</sub>	—	8.0	pF
<b>SWITCHING CHARACTERISTICS</b>				
Delay Time (V <sub>DD</sub> = 10 V <sub>dc</sub> , I <sub>D(on)</sub> = 20 mAdc) (V <sub>G(on)</sub> = 0, V <sub>GS(off)</sub> = 10 V <sub>dc</sub> )	t <sub>d</sub>	—	6.0	ns
Rise Time (V <sub>DD</sub> = 10 V <sub>dc</sub> , I <sub>D(on)</sub> = 10 mAdc) (V <sub>GS(on)</sub> = 0, V <sub>GS(off)</sub> = 6.0 V <sub>dc</sub> ) (Figure 1)	t <sub>r</sub>	—	4.0	ns
Turn-Off Time (V <sub>DD</sub> = 10 V <sub>dc</sub> , I <sub>D(on)</sub> = 5.0 mAdc) (V <sub>GS(on)</sub> = 0, V <sub>GS(off)</sub> = 4.0 V <sub>dc</sub> ) (Figure 1)	t <sub>off</sub>	—	50	ns

(1) Pulse Test: Pulse Width = 100 ms, Duty Cycle ≤ 10%.

FIGURE 1 — SWITCHING TIMES TEST CIRCUIT



TEST CIRCUIT



- NOTES: 1. The input waveforms are supplied by a generator with the following characteristics:  
 $Z_{out} = 50$  ohms, Duty Cycle  $\approx 2.0\%$
2. Waveforms are monitored on an oscilloscope with the following characteristics:  
 $t_r \leq 0.75$  ns,  $R_{in} \geq 1.0$  megohm,  $C_{in} \leq 2.5$  pF.